



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- $BV_{CEO} > 80V$
- $I_C = 1A$ High Continuous Collector Current
- $I_{CM} = 2A$ Peak Pulse Current
- 2W Power Dissipation
- Low Saturation Voltage $V_{CE(SAT)} < 500mV @ 0.5A$

Applications

- Medium Power Switching or Amplification Applications
- AF Driver and Output Stages

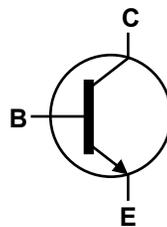
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads.
Solderable per MIL-STD-202, Method 208 
- Weight: 0.112 grams (Approximate)

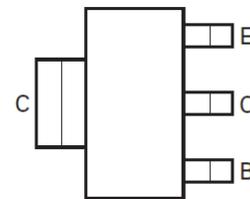
SOT223



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	1	A
Peak Pulse Collector Current	I_{CM}	2	
Continuous Base Current	I_B	100	mA
Peak Pulse Base Current	I_{BM}	200	

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

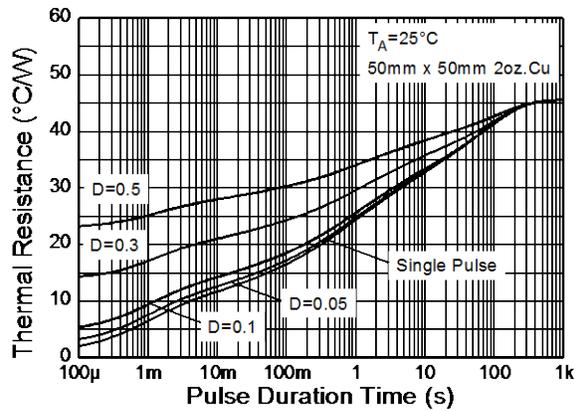
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	2.5	W
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	45.6	$^\circ\text{C/W}$
Thermal Resistance, Junction to Leads	(Note 6)	$R_{\theta JL}$	21.7	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 7)

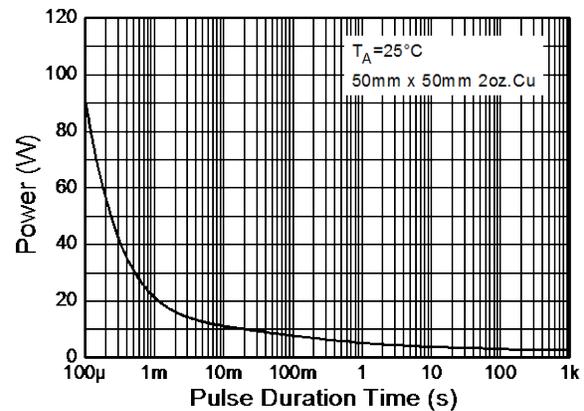
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
 6. Thermal resistance from junction to solder-point (at the end of the collector lead).
 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

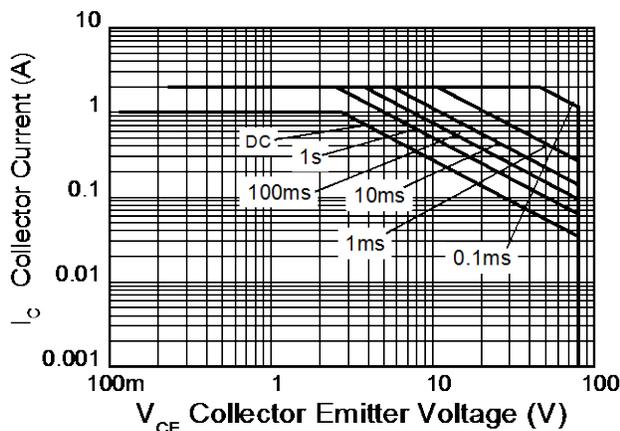
Thermal Characteristics and Derating Information



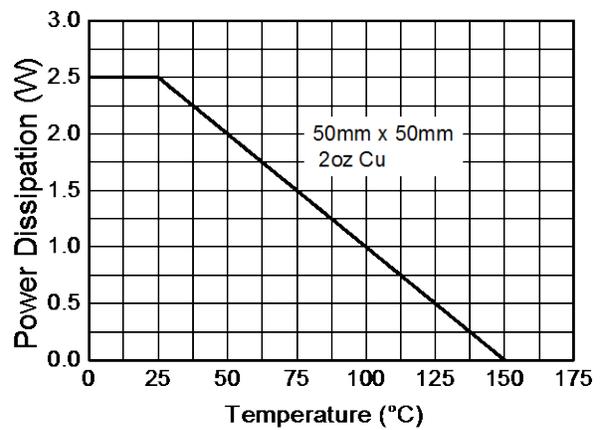
Transient Thermal Impedance



Pulse Power Dissipation



SOA, Safe Operating Area



Derating Curve

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	100	—	—	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 8)	BV_{CEO}	80	—	—	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	—	—	V	$I_E = 10\mu\text{A}$
Collector Cut-Off Current	I_{CBO}	—	—	0.1 20	μA	$V_{CB} = 30\text{V}$ $V_{CB} = 30\text{V}, T_A = +150^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}	—	—	20	nA	$V_{EB} = 6\text{V}$
Static Forward Current Transfer Ratio (Note 8)	h_{FE}	63 100 40	—	250	—	$I_C = 5\text{mA}, V_{CE} = 2\text{V}$ $I_C = 150\text{mA}, V_{CE} = 2\text{V}$ $I_C = 500\text{mA}, V_{CE} = 2\text{V}$
Collector-Emitter Saturation Voltage (Note 8)	$V_{CE(sat)}$	—	—	0.5	V	$I_C = 500\text{mA}, I_B = 50\text{mA}$
Base-Emitter Turn-On Voltage (Note 8)	$V_{BE(on)}$	—	—	1.0	V	$I_C = 500\text{mA}, V_{CE} = 2\text{V}$
Transition Frequency	f_r	100	150	—	MHz	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}	—	—	25	pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

 Note: 8. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

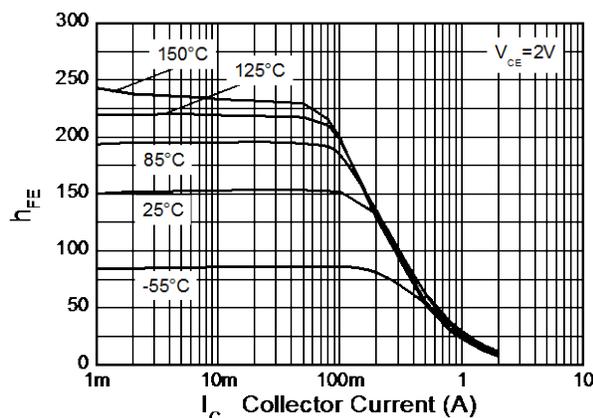
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)


Fig.1 : Typical DC Current Gain vs Collector Current

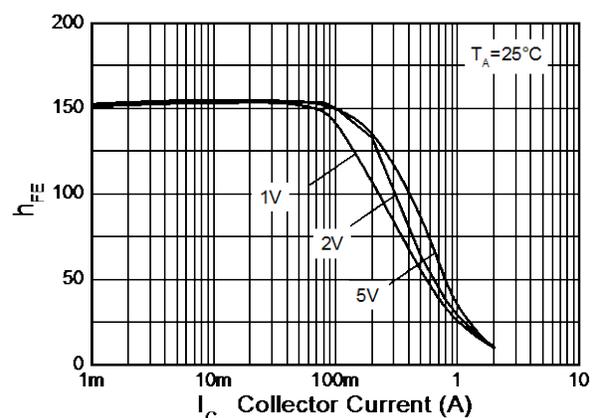


Fig.2 : Typical DC Current Gain vs Collector Current

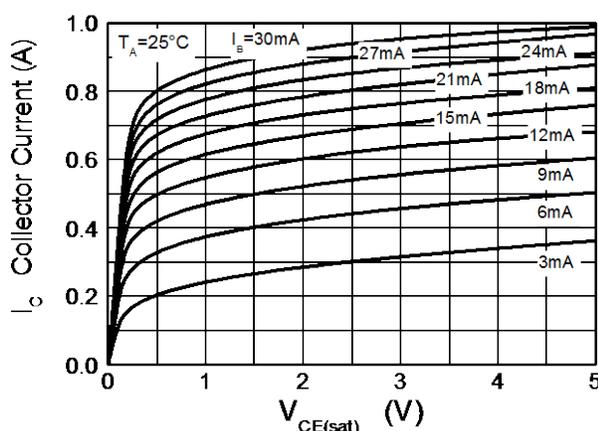


Fig.3 : Typical Collector Current vs Collector-Emitter Saturation Voltage

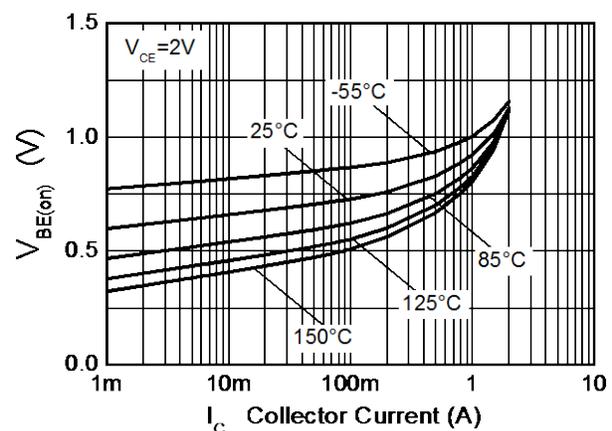


Fig.4 : Typical Base-Emitter Turn-On Voltage vs Collector Current

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

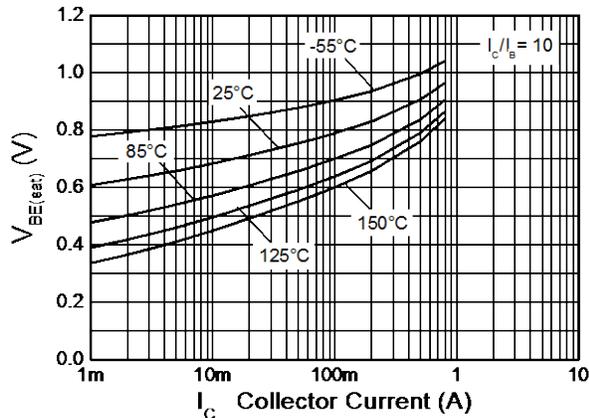


Fig 5: Typical Base-Emitter Saturation Voltage vs Collector Current

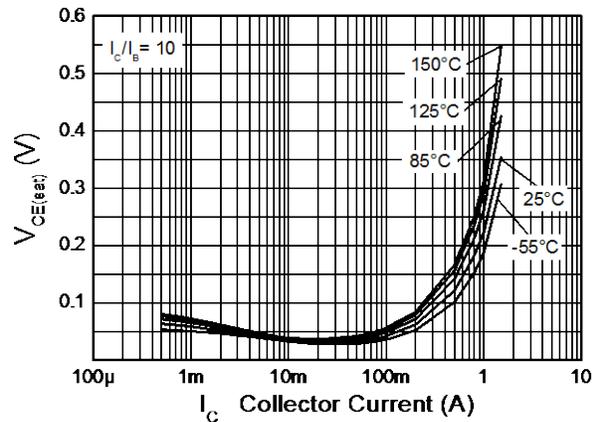


Fig 6: Typical Collector-Emitter Saturation Voltage vs Collector Current

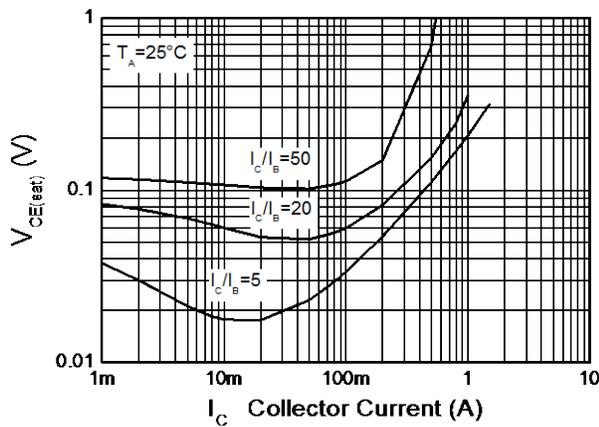


Fig 7: Typical Collector-Emitter Saturation Voltage vs Collector Current

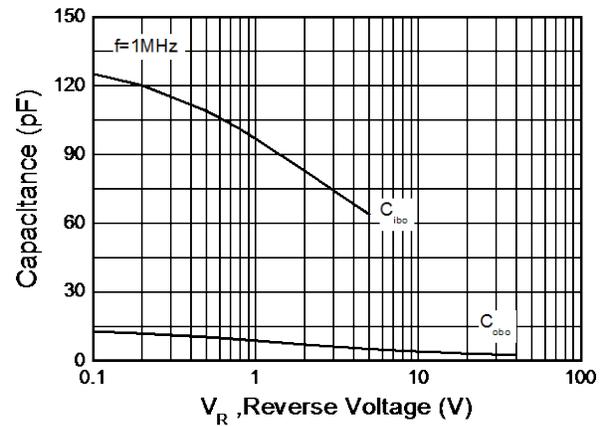
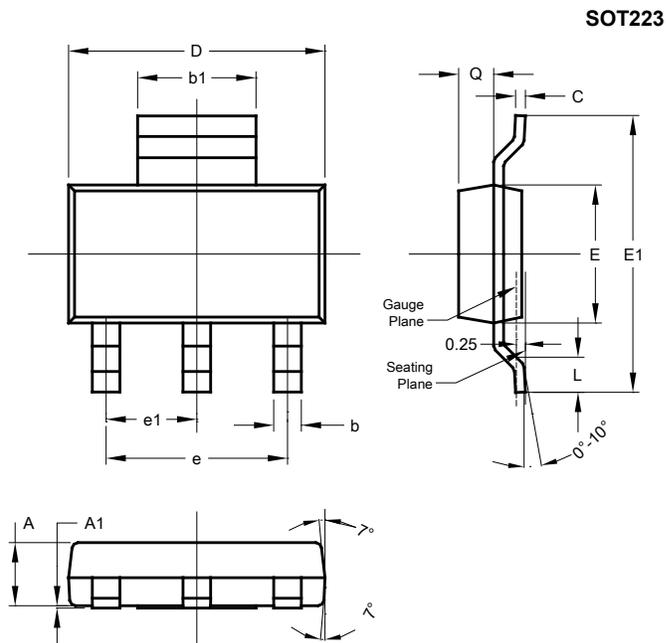


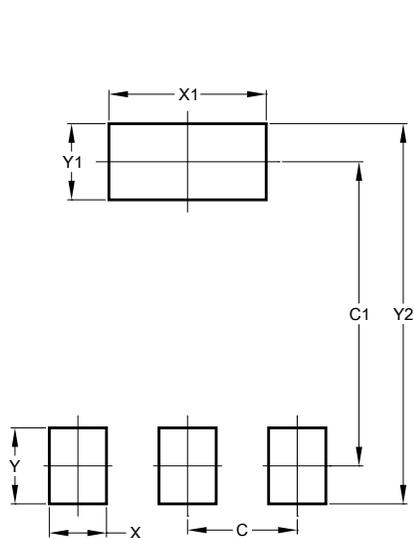
Fig 8: Typical Capacitance Characteristics

Package Outline Dimensions



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00